L Number	Hits	Search Text	DB	Time stamp
7	104	organic adj2 switch$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:55
9	17	(organic adj2 switch$3) and (first adj3 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:56
10	15	((organic adj2 switch$3) and (first adj3 electrode)) and (second adj3 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:14
11	219	(first adj3 electrode) same organic same diod$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:59
12	10	((first adj3 electrode) same organic same diod$2) same (second adj3 electrode) same memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:59
8	7	(organic adj2 switch$3) same (first adj3 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:17
14	2	("6055180").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:17
13	73	"6055180"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:22
15	23	tanabe-takahisa.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:23
16	0	tanabe-takahisa-$.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:23
-	10	organic adj3 switch$3 adj3 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 11:56
-	115	organic same (switch$3 adj2 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 11:56
-	5	(organic same (switch$3 adj2 memory)) same (first adj2 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 11:57

-	16	(first adj2 electrod$2) same (organic adj3 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:01
-	11	(organic same (switch$3 adj2 memory)) and ((first adj2 electrod$2) same (organic adj3 memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:01
-	39	(first adj2 electrod$2) and (organic adj3 memory) and (second electrod$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:01
-	22	((first adj2 electrod$2) and (organic adj3 memory) and (second electrod$2)) and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:02
-	11	(((first adj2 electrod$2) and (organic adj3 memory) and (second electrod$2)) and diode) and (organic same (switch$3 adj2 memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:07
-	19	(diode adj2 layer) near5 (second adj2 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:07
-	15	((diode adj2 layer) near5 (second adj2 electrode)) near5 (first adj2 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:07
-	7	((((diode adj2 layer) near5 (second adj2 electrode)) near5 (first adj2 electrode)) near10 organic) and (memory or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:10
-	14	(((diode adj2 layer) near5 (second adj2 electrode)) near5 (first adj2 electrode)) near10 organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:09
-	0	(low adj2 electrode) same (up adj2 electrode) same diode same resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:11
-	0	(low adj2 electrode) same (up adj2 electrode) same diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:12
-	3784	((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:13
-	141	(((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:17
-	5	((((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory) same (organic adj2 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:16

-	4	((((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory) same (organic adj2 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:17
-	36	((((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory) and 365/$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:53